

DirectFET® N-Channel Power MOSFET

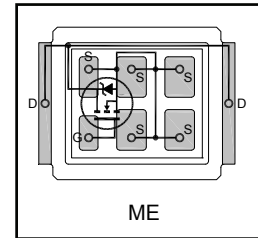
**Application**

- Brushed motor drive applications
- BLDC motor drive applications
- Battery powered circuits
- Half-bridge and full-bridge topologies
- Synchronous rectifier applications
- Resonant mode power supplies
- OR-ing and redundant power switches
- DC/DC and AC/DC converters
- DC/AC inverters

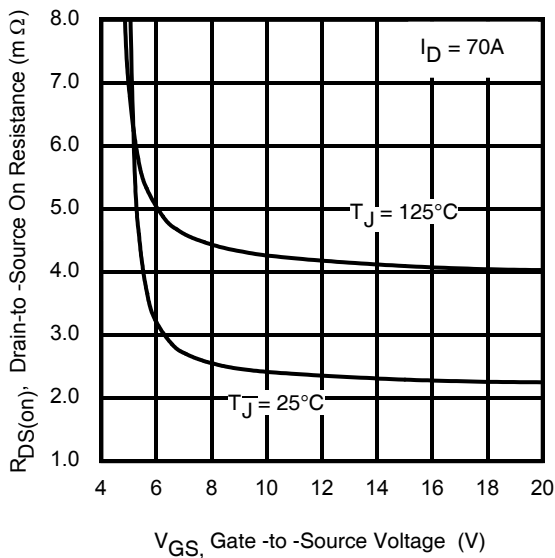
**Benefits**

- Improved gate, avalanche and dynamic dv/dt ruggedness
- Fully characterized capacitance and avalanche SOA
- Enhanced body diode dv/dt and di/dt capability
- Lead-free, RoHS compliant

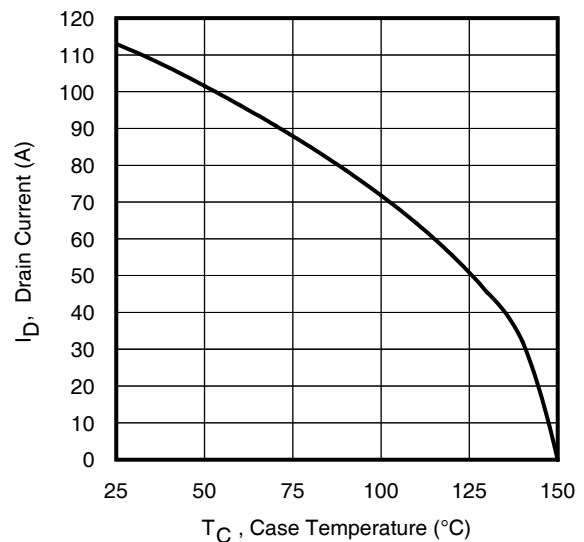
<b>V<sub>DSS</sub></b>	<b>60V</b>
<b>R<sub>DS(on)</sub> typ.</b>	<b>2.9mΩ</b>
	<b>3.6mΩ</b>
<b>I<sub>D</sub></b>	<b>114A</b>



Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF7580MPbF	DirectFET® ME	Tape and Reel	4800	IRF7580MTRPbF



**Fig 1.** Typical On-Resistance vs. Gate Voltage



**Fig 2.** Maximum Drain Current vs. Case Temperature

**Absolute Maximum Ratings**

Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	114	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	72	
$I_{DM}$	Pulsed Drain Current ①	452	
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	96	W
	Linear Derating Factor	0.78	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 150	°C

**Avalanche Characteristics**

$E_{AS}$ (Thermally limited)	Single Pulse Avalanche Energy ②	81	mJ
$E_{AS}$ (Thermally limited)	Single Pulse Avalanche Energy ③	149	
$I_{AR}$	Avalanche Current ①	See Fig.15,16 , 23a, 23b	A
$E_{AR}$	Repetitive Avalanche Energy ①		mJ

**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ① ⑦	—	44	°C/W
$R_{\theta JA}$	Junction-to-Ambient ③	12.5	—	
$R_{\theta JA}$	Junction-to-Ambient ②	20	—	
$R_{\theta JC}$	Junction-to-Case ④ ⑧	—	1.3	
$R_{\theta J-PCB}$	Junction-to-PCB Mounted ②	0.75	—	

**Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

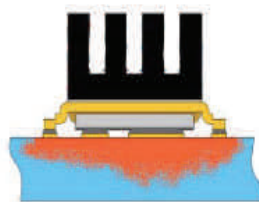
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	60	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	44	—	mV/°C	Reference to $25^\circ\text{C}, I_D = 1.0\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	2.9	3.6	mΩ	$V_{GS} = 10\text{V}, I_D = 70\text{A}$ ④
		—	3.5	—	mΩ	$V_{GS} = 6.0\text{V}, I_D = 35\text{A}$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.1	—	3.7	V	$V_{DS} = V_{GS}, I_D = 150\mu\text{A}$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$
		—	—	150	μA	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20\text{V}$
	Gate-to-Source Reverse Leakage	—	—	-100	nA	$V_{GS} = -20\text{V}$
$R_G$	Internal Gate Resistance	—	0.8	—	Ω	

**Notes:**

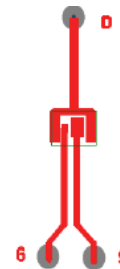
- ② Mounted on minimum footprint full size board with metalized back and with small clip heatsink.
- ③ Used double sided cooling , mounting pad with large heatsink.
- ④ TC measured with thermocouple mounted to top (Drain) of part.



- ① Surface mounted on 1 in. square Cu board (still air).



- ② Mounted to a PCB with small clip heatsink (still air)

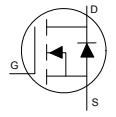


- ③ Mounted on minimum footprint full size board with metalized back and with small clip heatsink (still air)

**Dynamic @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

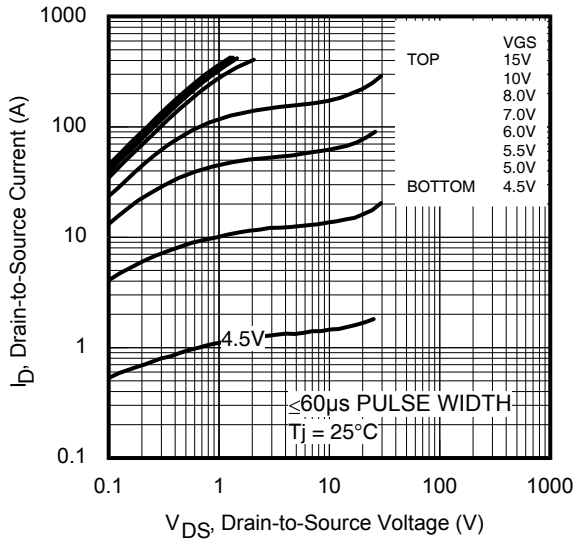
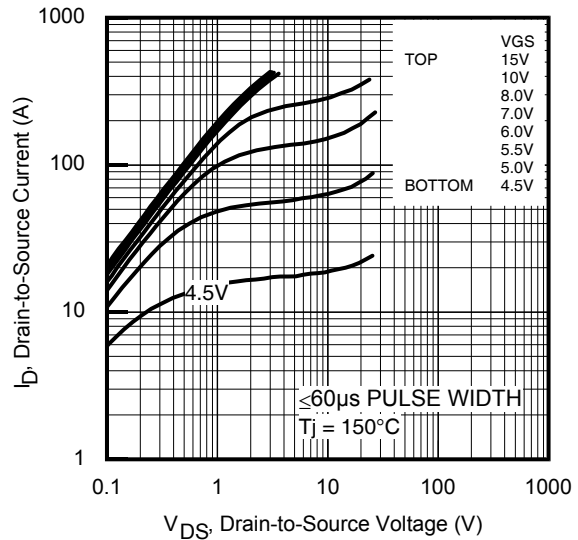
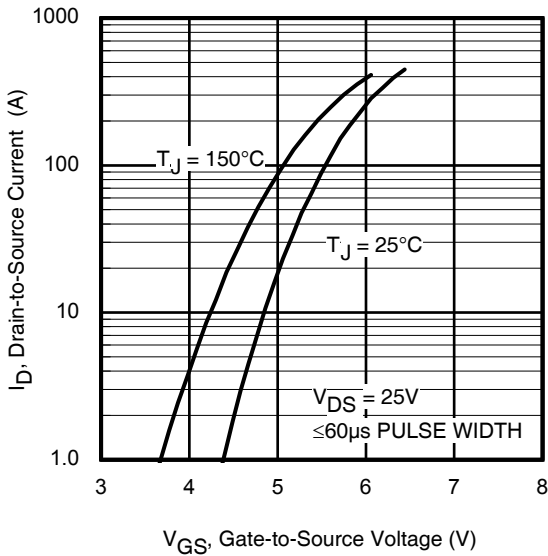
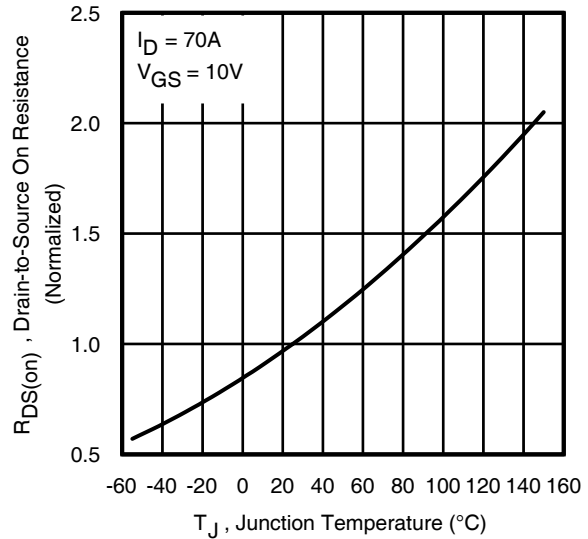
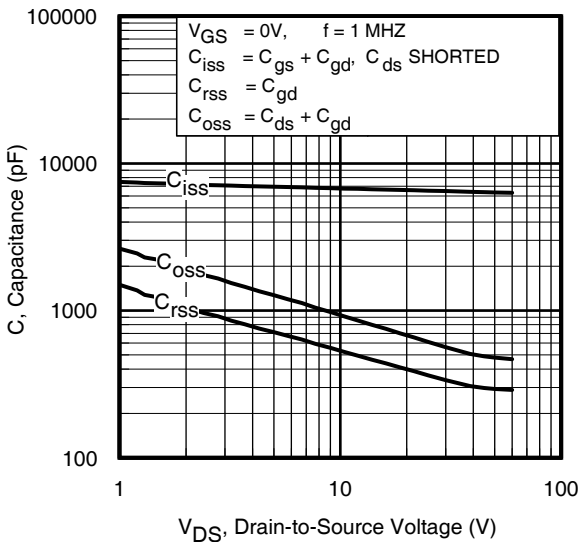
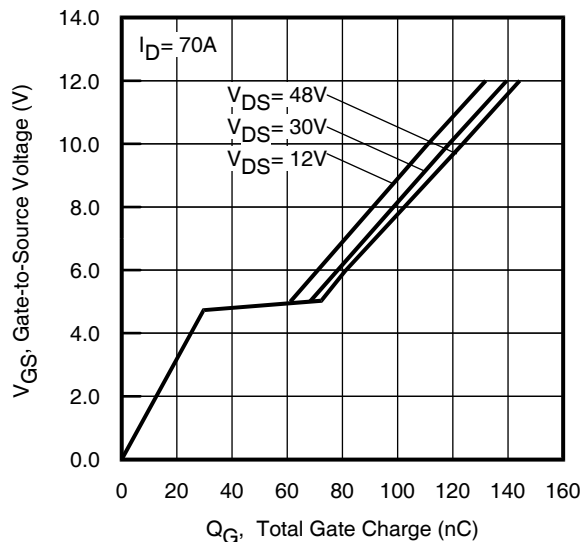
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$g_{fs}$	Forward Transconductance	190	—	—	S	$V_{DS} = 10V, I_D = 70A$
$Q_g$	Total Gate Charge	—	120	180	nC	$I_D = 70A$ $V_{DS} = 30V$ $V_{GS} = 10V$ ④
$Q_{gs}$	Gate-to-Source Charge	—	32	—		
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	36	—		
$Q_{sync}$	Total Gate Charge Sync. ( $Q_g - Q_{gd}$ )	—	84	—		
$t_{d(on)}$	Turn-On Delay Time	—	20	—	ns	$V_{DD} = 30V$ $I_D = 30A$ $R_G = 2.7\Omega$ $V_{GS} = 10V$ ④
$t_r$	Rise Time	—	38	—		
$t_{d(off)}$	Turn-Off Delay Time	—	53	—		
$t_f$	Fall Time	—	21	—		
$C_{iss}$	Input Capacitance	—	6510	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0MHz$ $V_{GS} = 0V, V_{DS} = 0V$ to 48V ⑥ $V_{GS} = 0V, V_{DS} = 0V$ to 48V ⑤
$C_{oss}$	Output Capacitance	—	610	—		
$C_{rss}$	Reverse Transfer Capacitance	—	360	—		
$C_{oss}$ eff. (ER)	Effective Output Capacitance (Energy Related)	—	620	—		
$C_{oss}$ eff. (TR)	Effective Output Capacitance (Time Related)	—	770	—		

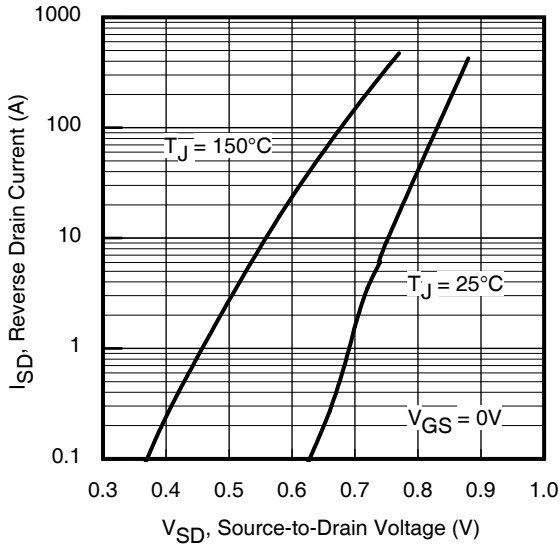
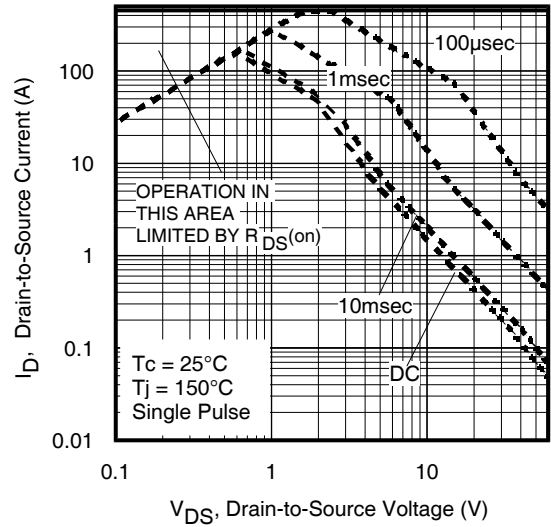
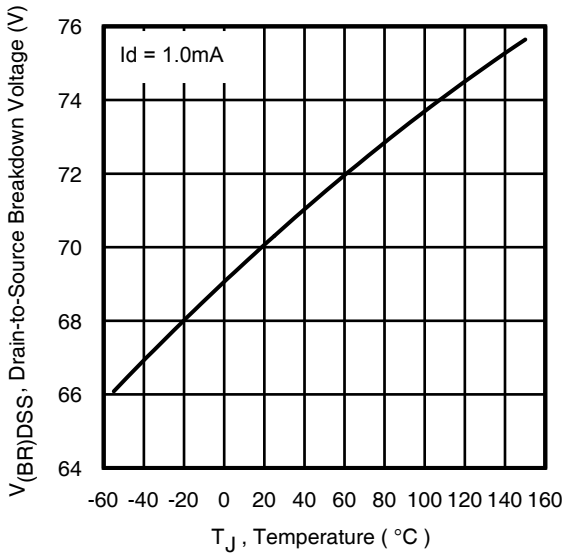
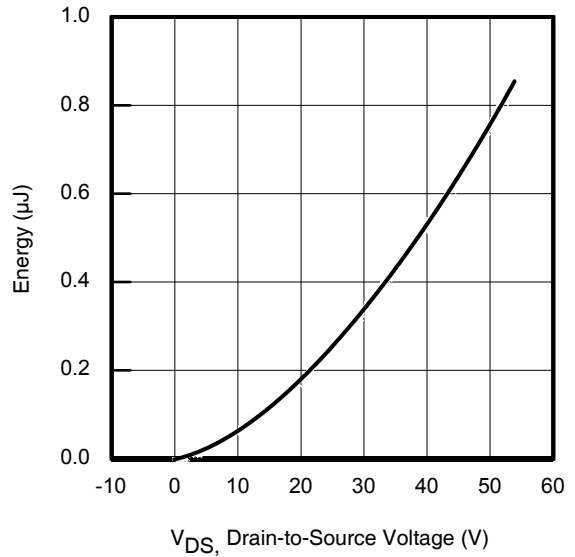
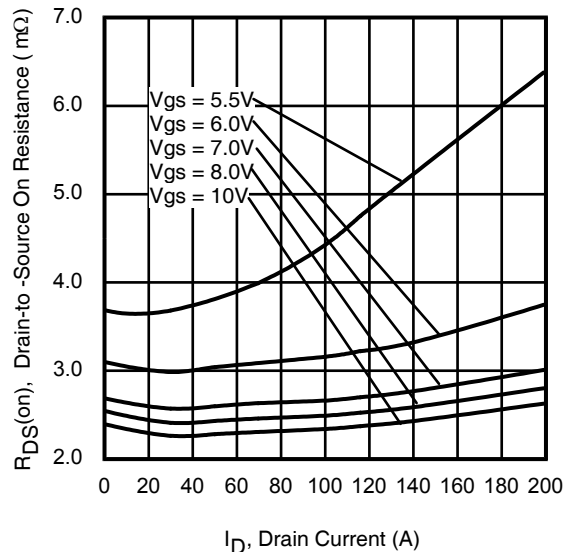
**Diode Characteristics**

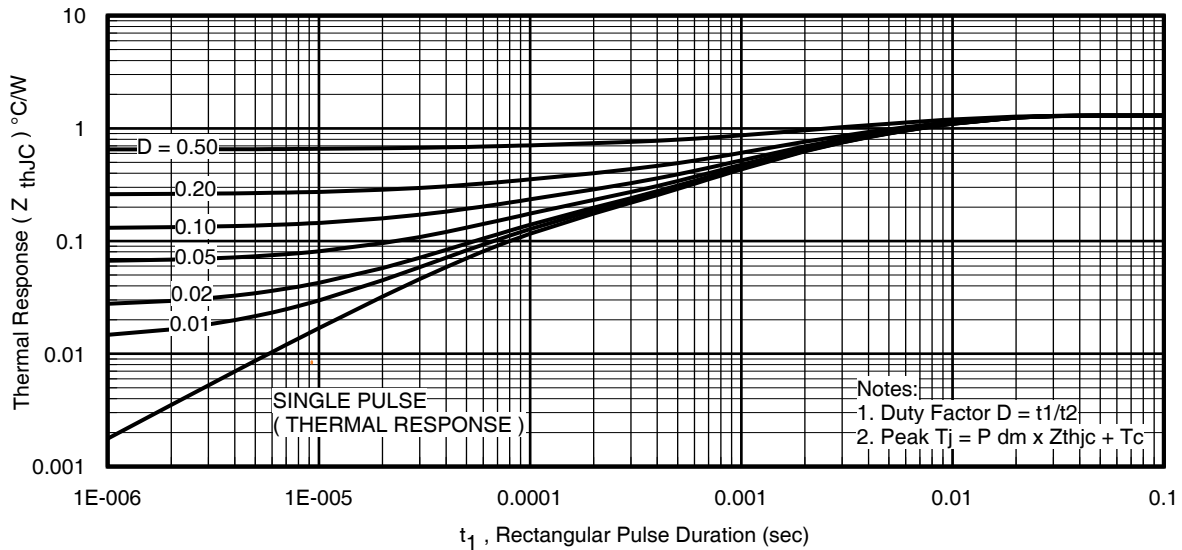
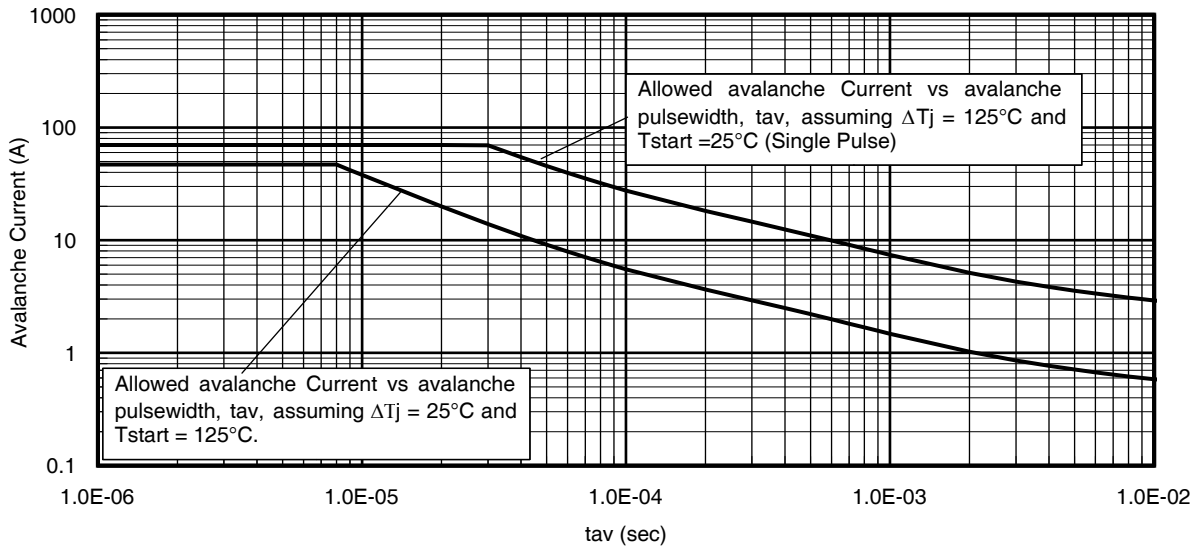
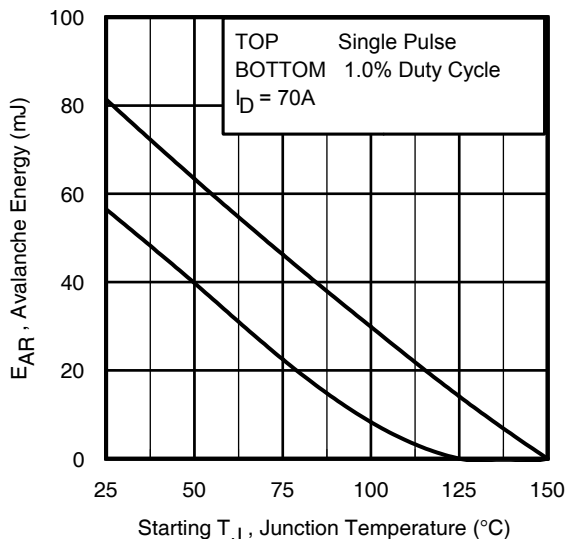
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	105	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	460		
$V_{SD}$	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}, I_S = 70A, V_{GS} = 0V$ ④
$dv/dt$	Peak Diode Recovery ③	—	4.1	—	V/ns	$T_J = 150^\circ\text{C}, I_S = 70A, V_{DS} = 60V$
$t_{rr}$	Reverse Recovery Time	—	41	—	ns	$T_J = 25^\circ\text{C}$ $V_R = 51V,$ $T_J = 125^\circ\text{C}$ $I_F = 70A$
$Q_{rr}$	Reverse Recovery Charge	—	55	—		
		—	71	—	nC	$T_J = 25^\circ\text{C}$ $di/dt = 100A/\mu s$ ④ $T_J = 125^\circ\text{C}$
$I_{RRM}$	Reverse Recovery Current	—	2.5	—	A	$T_J = 25^\circ\text{C}$

**Notes:**

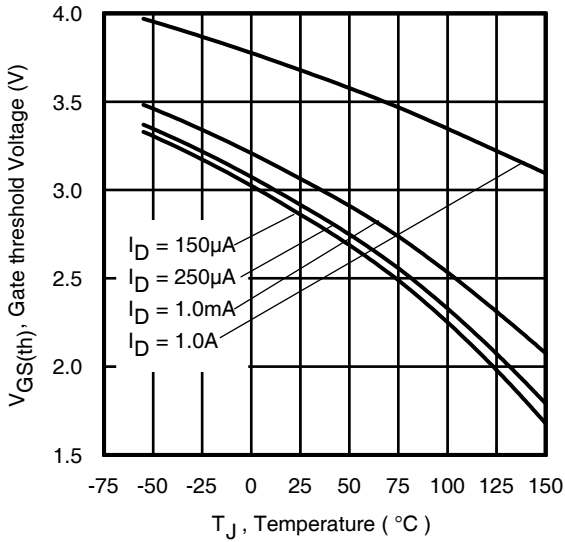
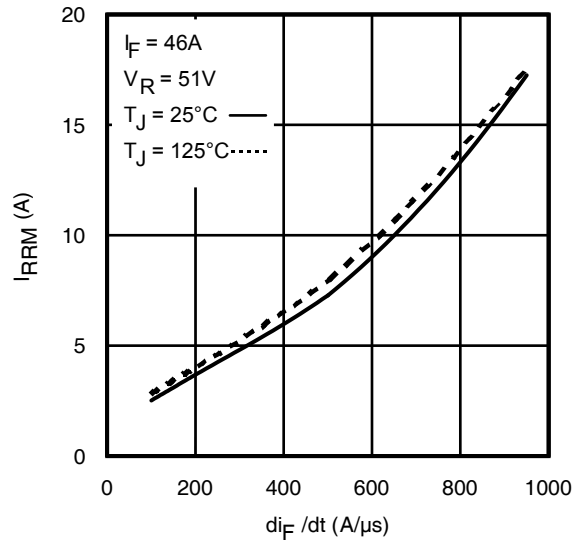
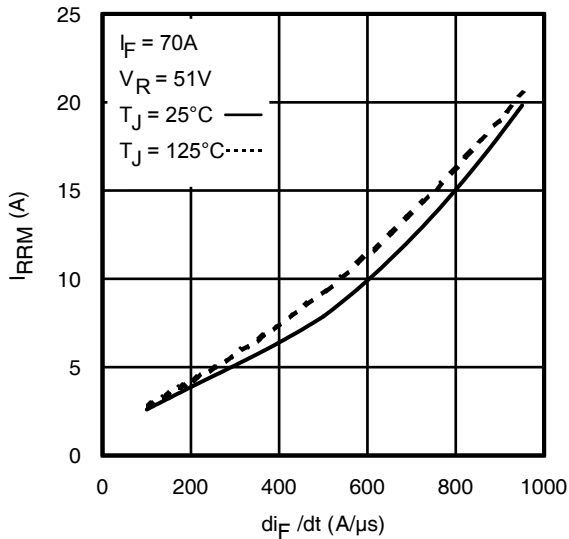
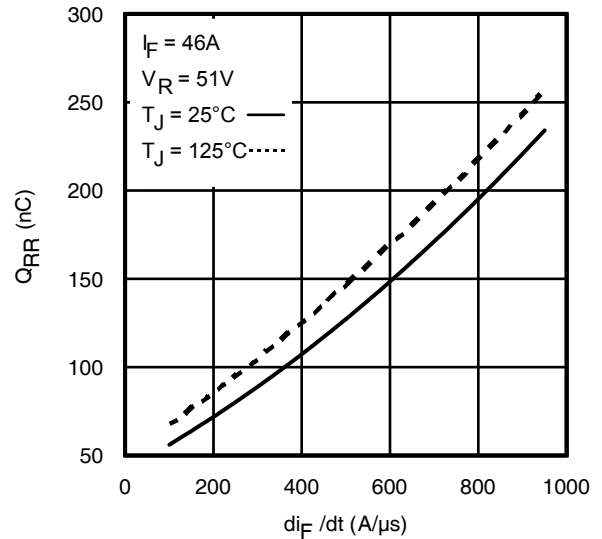
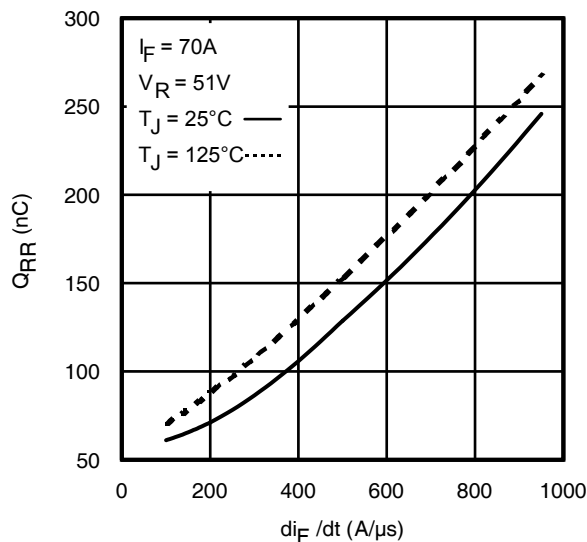
- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by  $T_J$  max, starting  $T_J = 25^\circ\text{C}$ ,  $L = 34\mu H$   
 $R_G = 50\Omega, I_{AS} = 70A, V_{GS} = 10V$ .
- ③  $I_{SD} \leq 70A, di/dt \leq 980A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150^\circ\text{C}$ .
- ④ Pulse width  $\leq 400\mu s$ ; duty cycle  $\leq 2\%$ .
- ⑤  $C_{oss}$  eff. (TR) is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑥  $C_{oss}$  eff. (ER) is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑧  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$ .
- ⑨ Limited by  $T_J$  max, starting  $T_J = 25^\circ\text{C}$ ,  $L = 1mH, R_G = 50\Omega, I_{AS} = 17A, V_{GS} = 10V$ .

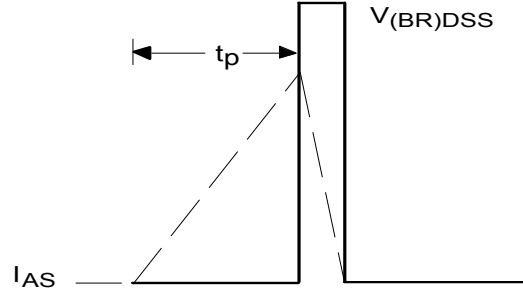
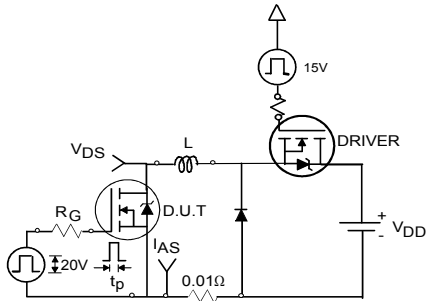
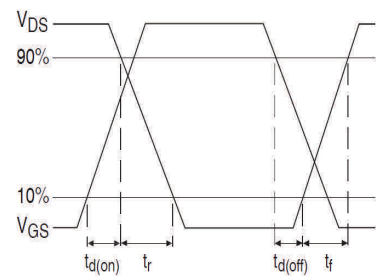
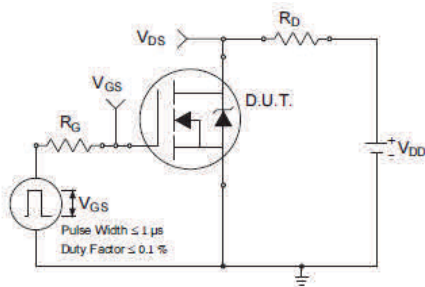
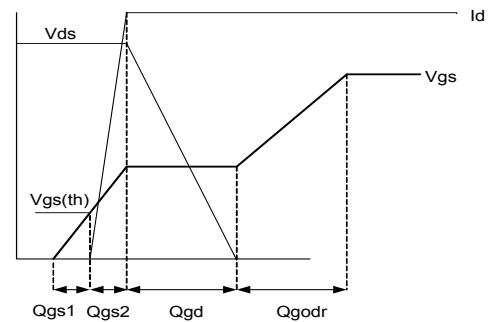
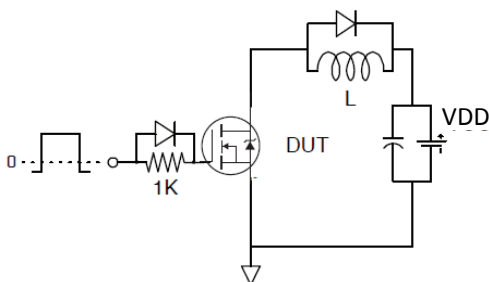

**Fig 3. Typical Output Characteristics**

**Fig 4. Typical Output Characteristics**

**Fig 5. Typical Transfer Characteristics**

**Fig 6. Normalized On-Resistance vs. Temperature**

**Fig 7. Typical Capacitance vs. Drain-to-Source Voltage**

**Fig 8. Typical Gate Charge vs. Gate-to-Source Voltage**


**Fig 9.** Typical Source-Drain Diode Forward Voltage

**Fig 10.** Maximum Safe Operating Area

**Fig 11.** Drain-to-Source Breakdown Voltage

**Fig 12.** Typical  $C_{oss}$  Stored Energy

**Fig 13.** Typical On-Resistance vs. Drain Current


**Fig 14. Maximum Effective Transient Thermal Impedance, Junction-to-Case**

**Fig 15. Avalanche Current vs. Pulse Width**

**Fig 16. Maximum Avalanche Energy vs. Temperature**
**Notes on Repetitive Avalanche Curves , Figures 15, 16:  
(For further info, see AN-1005 at www.irf.com)**

1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 23a, 23b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 14, 15).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see Figures 13)  
 $P_{D(ave)} = 1/2 ( 1.3 \cdot BV \cdot I_{av} ) = \Delta T / Z_{thJC}$   
 $I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$   
 $E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$

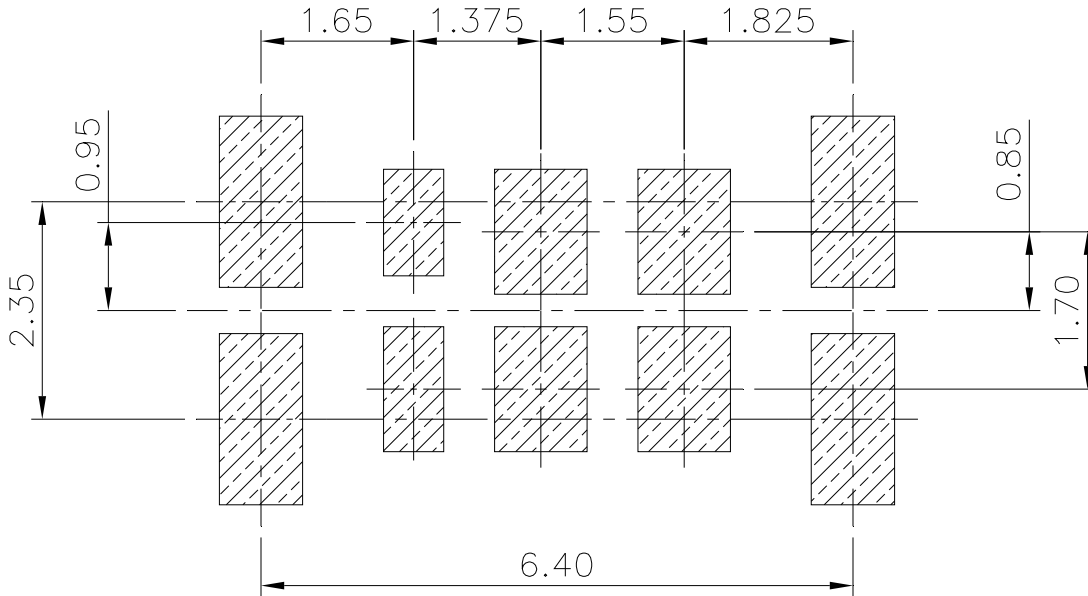

**Fig 17.** Threshold Voltage vs. Temperature

**Fig 18.** Typical Recovery Current vs. dif/dt

**Fig 19.** Typical Recovery Current vs. dif/dt

**Fig 20.** Typical Stored Charge vs. dif/dt

**Fig 21.** Typical Stored Charge vs. dif/dt


**Fig 22. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs**

**Fig 23a. Unclamped Inductive Test Circuit**
**Fig 23b. Unclamped Inductive Waveforms**

**Fig 24a. Switching Time Test Circuit**
**Fig 24b. Switching Time Waveforms**

**Fig 25a. Gate Charge Test Circuit**
**Fig 25b. Gate Charge Waveform**

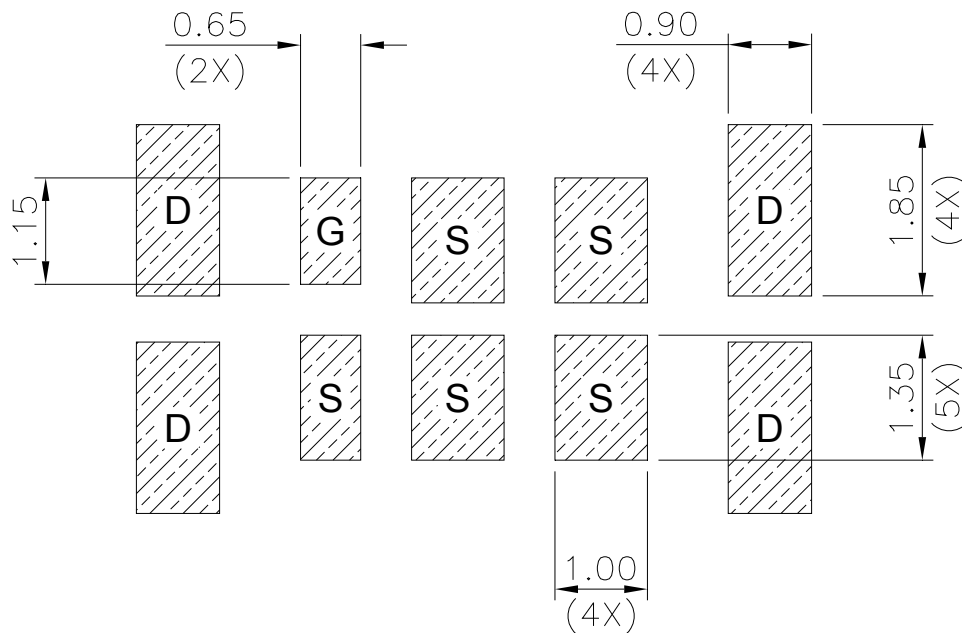


**DirectFET<sup>®</sup> Board Footprint, ME Outline  
(Medium Size Can, E-Designation)**

Please see DirectFET<sup>®</sup> application note AN-1035 for all details regarding the assembly of DirectFET<sup>®</sup>. This includes all recommendations for stencil and substrate designs.



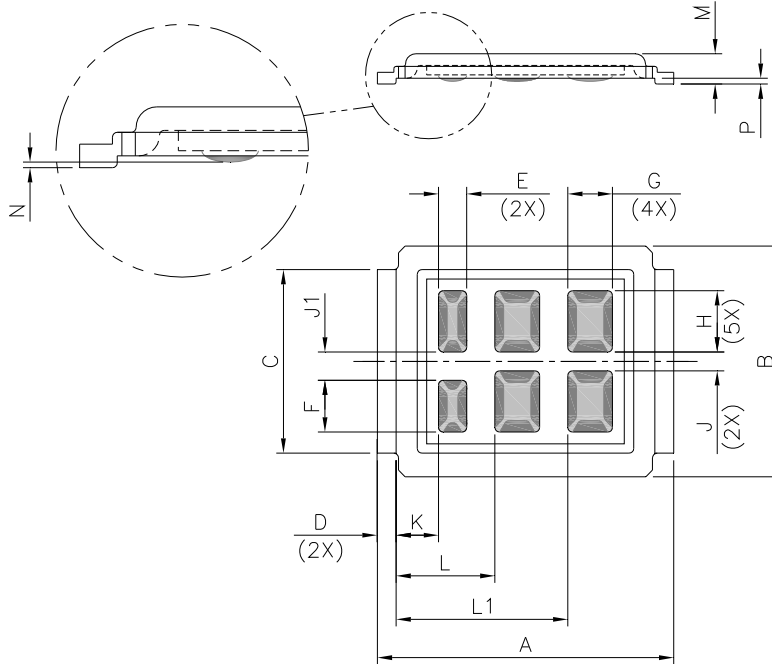
**G = GATE**  
**D = DRAIN**  
**S = SOURCE**



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

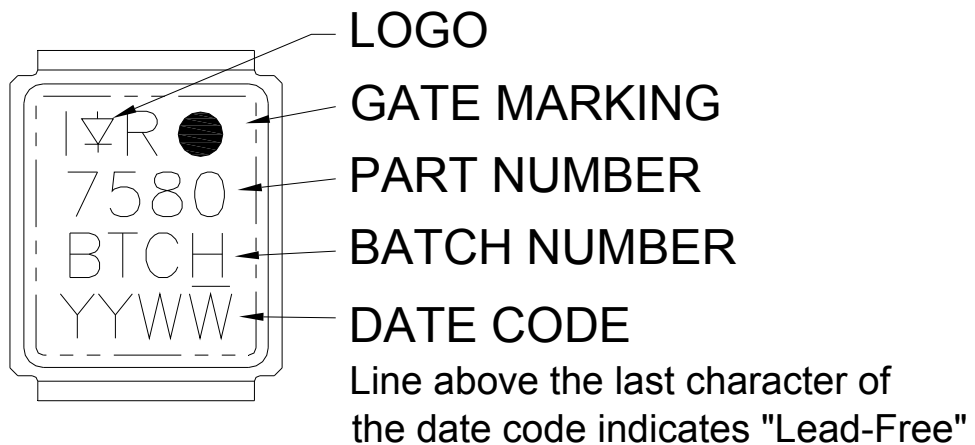
**DirectFET® Outline Dimension, ME Outline  
(Medium Size Can, E-Designation)**

Please see DirectFET® application note AN-1035 for all details regarding the assembly of DirectFET®. This includes all recommendations for stencil and substrate designs.

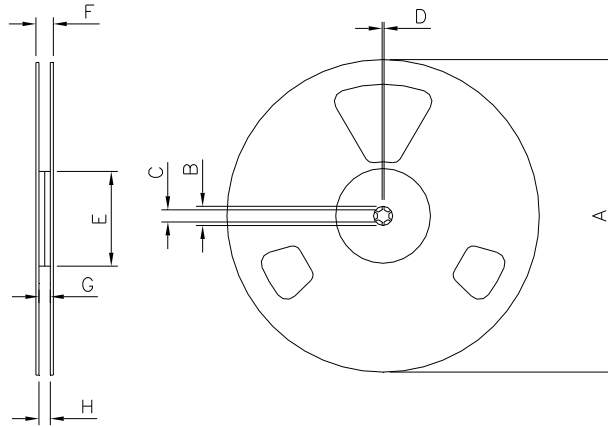


CODE	METRIC		IMPERIAL	
	MIN	MAX	MIN	MAX
A	6.25	6.35	0.246	0.250
B	4.80	5.05	0.189	0.199
C	3.85	3.95	0.152	0.156
D	0.35	0.45	0.014	0.018
E	0.58	0.62	0.023	0.024
F	1.08	1.12	0.043	0.044
G	0.93	0.97	0.037	0.038
H	1.28	1.32	0.050	0.052
J	0.38	0.42	0.015	0.017
J1	0.58	0.62	0.023	0.024
K	0.88	0.92	0.035	0.036
L	2.08	2.12	0.082	0.083
L1	3.63	3.67	0.143	0.144
M	0.59	0.70	0.023	0.028
N	0.02	0.08	0.0008	0.003
P	0.08	0.17	0.003	0.007

Dimensions are shown in millimeters (inches)

**DirectFET® Part Marking**


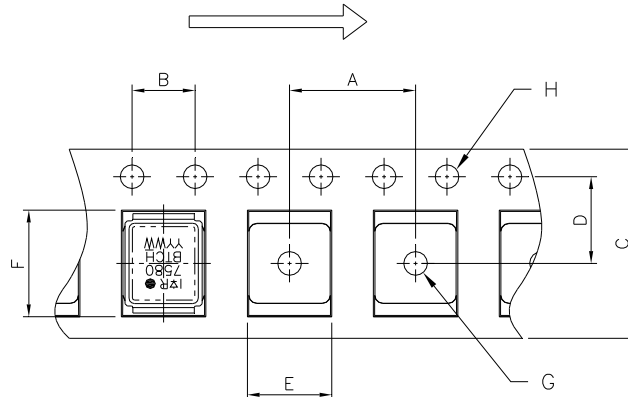
Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

**DirectFET® Tape & Reel Dimension (Showing component orientation).**


NOTE: Controlling dimensions in mm  
 Std reel quantity is 4800 parts. (ordered as IRF7580MTRPbF). For 1000 parts on 7" reel, order IRF7580MTR1PbF

REEL DIMENSIONS								
CODE	STANDARD OPTION (QTY 4800)				TR1 OPTION (QTY 1000)			
	METRIC		IMPERIAL		METRIC		IMPERIAL	
	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX
A	330.0	N.C	12.992	N.C	177.77	N.C	6.9	N.C
B	20.2	N.C	0.795	N.C	19.06	N.C	0.75	N.C
C	12.8	13.2	0.504	0.520	13.5	12.8	0.53	0.50
D	1.5	N.C	0.059	N.C	1.5	N.C	0.059	N.C
E	100.0	N.C	3.937	N.C	58.72	N.C	2.31	N.C
F	N.C	18.4	N.C	0.724	N.C	13.50	N.C	0.53
G	12.4	14.4	0.488	0.567	11.9	12.01	0.47	N.C
H	11.9	15.4	0.469	0.606	11.9	12.01	0.47	N.C

LOADED TAPE FEED DIRECTION



NOTE: CONTROLLING DIMENSIONS IN MM

CODE	DIMENSIONS			
	METRIC		IMPERIAL	
	MIN	MAX	MIN	MAX
A	7.90	8.10	0.311	0.319
B	3.90	4.10	0.154	0.161
C	11.90	12.30	0.469	0.484
D	5.45	5.55	0.215	0.219
E	5.10	5.30	0.201	0.209
F	6.50	6.70	0.256	0.264
G	1.50	N.C	0.059	N.C
H	1.50	1.60	0.059	0.063

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

**Qualification Information<sup>†</sup>**

<b>Qualification Level</b>	Industrial (per JEDEC JESD47F <sup>††</sup> guidelines)	
<b>Moisture Sensitivity Level</b>	DFET 1.5	MSL1 (per JEDEC J-STD-020D <sup>††</sup> )
<b>RoHS Compliant</b>	Yes	

† Qualification standards can be found at International Rectifier's web site  
<http://www.irf.com/product-info/reliability>

†† Applicable version of JEDEC standard at the time of product release.

\* Industrial qualification standards except autoclave test conditions.

**Revision History**

<b>Date</b>	<b>Comments</b>
3/25/2014	<ul style="list-style-type: none"> <li>Corrected figure 6 - Normalized On-Resistance vs. Temperature graph on page 4.</li> </ul>
2/19/2015	<ul style="list-style-type: none"> <li>Updated <math>E_{AS(L=1mH)} = 149mJ</math> on page 2</li> <li>Updated note 9 "Limited by <math>T_{Jmax}</math>, starting <math>T_J = 25^{\circ}C</math>, <math>L = 1mH</math>, <math>R_G = 50\Omega</math>, <math>I_{AS} = 17A</math>, <math>V_{GS} = 10V</math>" on page 3</li> </ul>
05/14/2015	<ul style="list-style-type: none"> <li>Updated registered trademark from DirectFET<sup>™</sup> to DirectFET<sup>®</sup> on page 1,9 and 10.</li> </ul>

International  
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Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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